

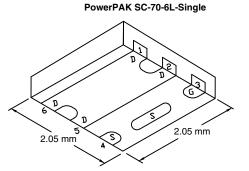
Vishay Siliconix

RoHS COMPLIANT

HALOGEN

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)			
30	0.019 at V _{GS} = 4.5 V	12	11.6			
	0.025 at V _{GS} = 2.5 V	12	11.0			

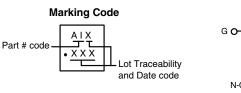


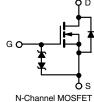
FEATURES

- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package - Small Footprint Area
- Typical ESD Performance 2500 V HBM
- 100 % R_g and UIS Tested
- FREE Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch, OVP Switch
- **Boost Converters**
- **DC/DC** Converters





Ordering Information:

SiA400EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 °C$ $T_{C} = 70 °C$ $T_{A} = 25 °C$ $T_{A} = 70 °C$	I _D	12 ^a 12 ^a 11 ^{b, c} 8.8 ^{b, c}	A	
Pulsed Drain Current (t = 300 µs)		I _{DM}	30		
Continuous Source-Drain Diode Current	T _C = 25 °C T _A = 25 °C	I _S	12 ^a 2.9 ^{b, c}		
Avalanche Current		I _{AS}	15		
Single Pulse Avalanche L = 0.1 mH		E _{AS}	11.25	mJ	
Maximum Power Dissipation $T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{A} = 25 \text{ °C}$ $T_{A} = 70 \text{ °C}$		P _D	19.2 12.3 3.5 ^{b, c} 2.2 ^{b, c}	w	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•	•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		34		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_{\rm D} = 250 \mu \text{A}$		- 3.8			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.6		1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 15	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1		
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	20			А	
Drain-Source On-State Resistance ^a	5	V _{GS} = 4.5 V, I _D = 11 A		0.016	0.019	Ω	
	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 9.6 A		0.019	0.025		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 11 A		50		S	
Dynamic ^b	<u> </u>		L				
Input Capacitance	C _{iss}		1	1265		pF	
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		132			
Reverse Transfer Capacitance	C _{rss}			80			
-		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		24	36	nC	
Total Gate Charge	Qg			11.6	17.4		
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A		2.9			
Gate-Drain Charge	Q _{gd}			2.2			
Gate Resistance	R _g	f = 1 MHz	0.6	3.3	6.6	Ω	
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_{1} = 1.7 \Omega$		23	35	- ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.8 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		26	39		
Fall Time	t _f			9	18		
Turn-On Delay Time	t _{d(on)}			4	8		
Rise Time	t _r	V_{DD} = 15 V, R_{L} = 1.7 Ω		14	21		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 8.8 \text{ A}, V_{GEN} = 10 \text{ V}, \text{R}_g = 1 \Omega$		25	38		
Fall Time	t _f			9	18		
Drain-Source Body Diode Characteristic	s			•			
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			12		
Pulse Diode Forward Current	I _{SM}				30	A	
Body Diode Voltage	V _{SD}	I _S = 8.8 A, V _{GS} = 0 V		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	23	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			7	14	nC	
Reverse Recovery Fall Time	t _a	$I_F = 8.8 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$		9		1	
Reverse Recovery Rise Time	t _b			6		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

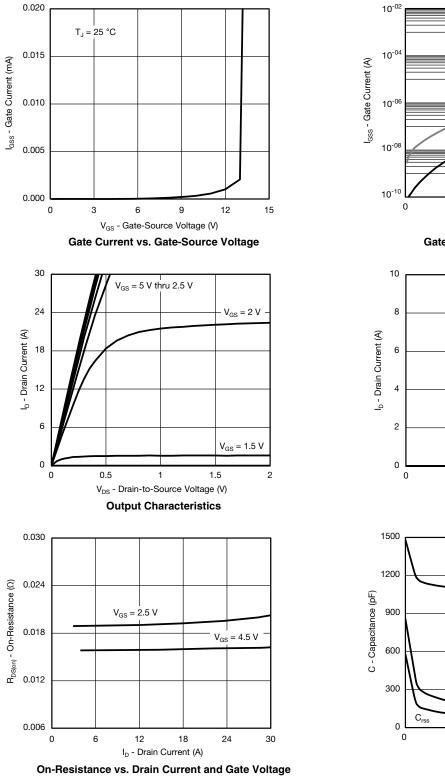
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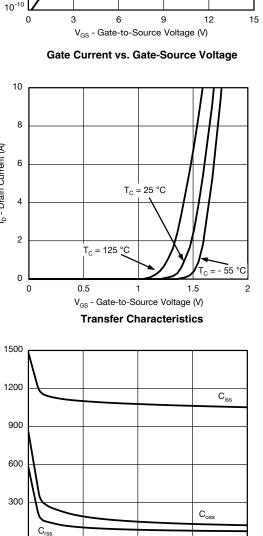
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





5

10

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

15

T_J = 150 °C

 $T_J = 25 \ ^{\circ}C$

20

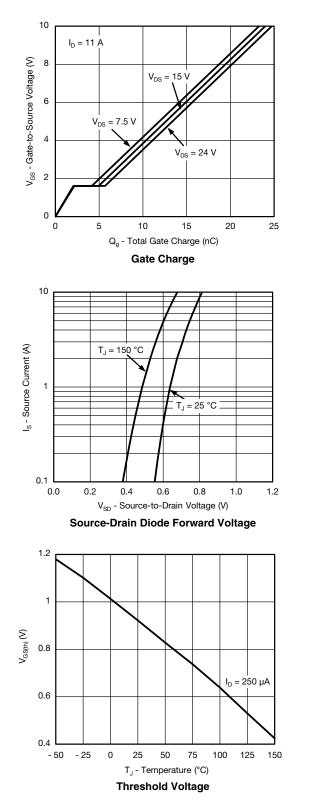
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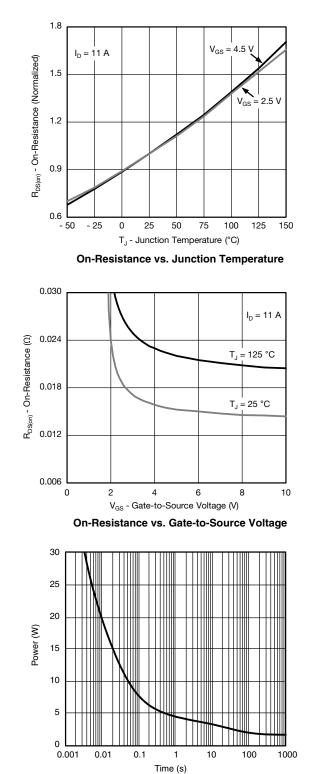
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Power (Junction-to-Ambient)

www.vishay.com 4 For technical questions, contact: pmostechsupport@vishay.com

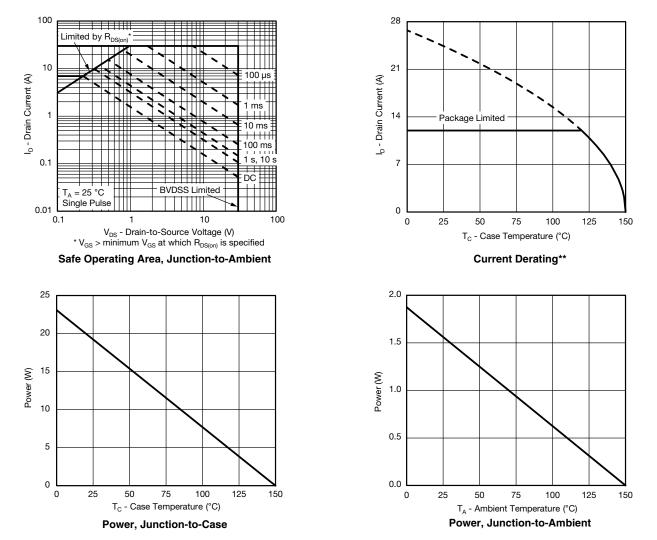
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SiA400EDJ Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



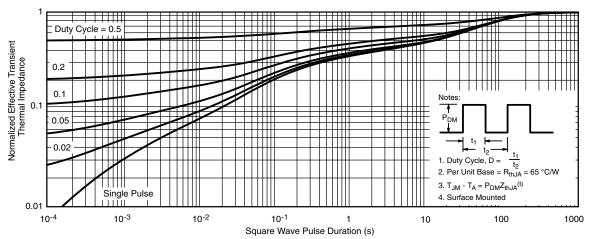
** The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiA400EDJ

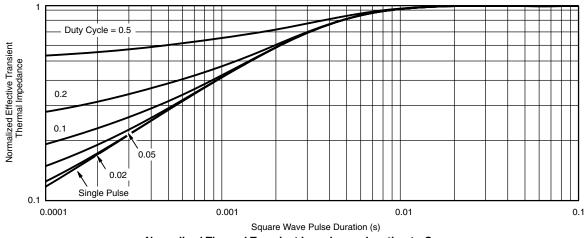


Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267844.

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PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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